



Claims

1. Transistor comprising elements of a bipolar static induction transistor - a gate, a source and a channel - on each of the sides of a substrate.

2. Transistor according to claim 1 differing in that one of the channels of multielement structures on each of the sides of the substrate is thicker than other channels, and this channel is connected to a separate electrode.

3. Transistor comprising on each of the sides of a lightly doped substrate an epitaxial layer of the same type of conductivity with the impurity concentration of about 10^{17} cm^{-3} , in which elements of a bipolar static induction transistor - a gate, a source and a channel - are disposed.

4. Transistor according to claim 3 differing in that one of the channels of multielement structures on each of sides of the substrate is thicker than other channels, and this channel is connected to a separate electrode.

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